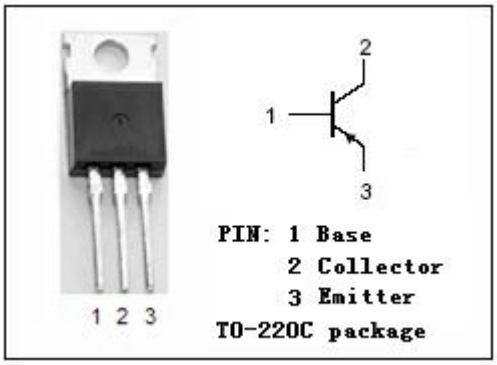
isc Silicon PNP Power Transistor 2SB521



DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -60V(Min)
- Low Collector Saturation Voltage-

: $V_{CE(sat)}$= -0.4V(Max.) @I_C= -3A

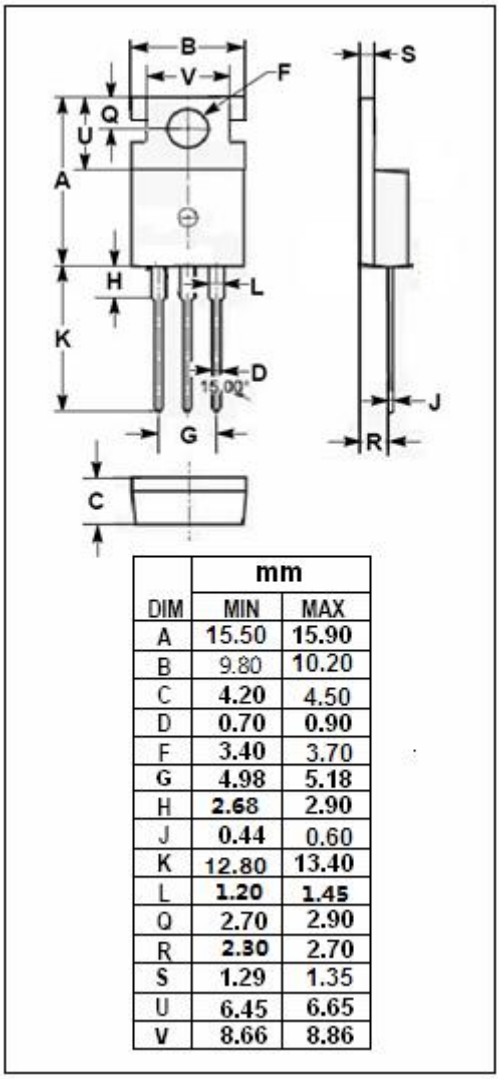
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high current switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-5	A
P_C	Collector Power Dissipation @Tc=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -10mA; I_B= 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-8			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.15A			-0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -0.15A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -50V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -8V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -2.5A; V_{CE}= -2V	50			
f_T	Current-Gain—Bandwidth Product	I_C=-0.2A ; V_{CE}= -5V		7		MHz